

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

ATTY. DOCKET NO.
60188-726

SERIAL NO.
Divisional of Appl. No.
09/895,213

APPLICANT
Shigeo YOSHII, et al.

(PTO-1449)

FILING DATE
January 09, 2004

GROUP

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
<i>[Handwritten initials]</i>		US 5,478,811	12/1995	Fujii et al.	
		US 6,350,997	02/2002	Saeki	
		US 5,159,603	10/1992	Kim	
		US 6,072,189	06/2000	Duggan	
		US 5,010,382	04/23/1991	Katoh	

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes-Number + -Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
		JP 60-167390	08/30/1985	Masamichi et al.	Yamanishi et al.		
		JP 61-231788	10/16/1986	Yoshihiro et al. →	Mori et al.		
		JP 61-270885	12/01/1986	Yoshiro et al.	Mori et al.		
		JP 62-189750	08/19/1987	Yoshiro et al.	Mori et al.		
		JP 62-244186	10/24/1987	Mototsugu et al.	Ogata et al.		
		JP 63-024692	02/02/1988	Shuichi Oluna			
		JP 61-059793	03/27/1986	Shibata et al.			
		JP 04-075347	03/10/1992	Okubo et al.			
		JP 02-280338	11/16/1990	Tanaka			
		JP 03-008340	01/16/1991	Kato			
		JP 61-053768	03/17/1986	Kato et al.			
	JP 61-131491	06/19/1986	Arai				

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
<i>[Handwritten initials]</i>		J. SHIBATA et al., "Fundamental Characteristics of an InGaAsP/InP Laser Transistor", Electronics Letters, Vol. 21, No. 3, January 31, 1985, pages 98-100.
		Y. MORI et al., "Operation Principle of the InGaAsP/InP Laser Transistor", Appl. Phys. Lett. 47(7), October 1, 1985, pages 649-651.

EXAMINER

J. MONDT

DATE CONSIDERED

05/04/05

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.